

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC2216, 2SC2717

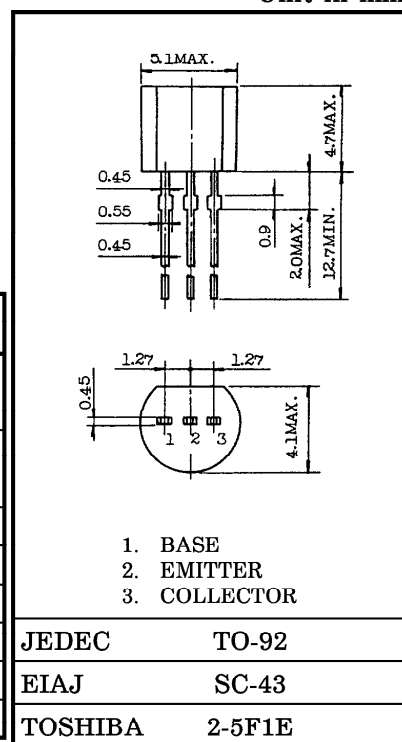
TV FINAL PICTURE IF AMPLIFIER APPLICATIONS.

Unit in mm

- High Gain : $G_{pe} = 33\text{dB}$ (Typ.) ($f = 45\text{MHz}$)
- Good Linearity of h_{FE} .

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	2SC2216	V _{CBO}	50	V
	2SC2717		30	
Collector-Emitter Voltage	2SC2216	V _{CEO}	45	V
	2SC2717		25	
Emitter-Base Voltage		V _{EBO}	4	V
Collector Current		I _C	50	mA
Emitter Current		I _E	−50	mA
Collector Power Dissipation		P _C	300	mW
Junction Temperature		T _j	125	°C
Storage Temperature Range		T _{stg}	−55~125	°C



Weight : 0.21g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	2SC2216	I_{CBO} $V_{CB} = 50\text{V}, I_E = 0$	—	—	0.1	μA
	2SC2717					
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 3\text{V}, I_C = 0$	—	—	0.1	μA
Collector-Emitter Breakdown Voltage	2SC2216	$V_{(BR)CEO}$ $I_C = 10\text{mA}, I_B = 0$	45	—	—	V
	2SC2717		25	—	—	
DC Current Gain	2SC2216	h_{FE} $V_{CE} = 12.5\text{V}, I_C = 12.5\text{mA}$	40	—	140	—
	2SC2717		40	—	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 15\text{mA}, I_B = 1.5\text{mA}$	—	—	0.2	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 15\text{mA}, I_B = 1.5\text{mA}$	—	—	1.5	V
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 30\text{MHz}$	0.8	—	2.0	pF
Collector-Base Time Constant	$C_c \cdot r_{bb'}$	$V_{CB} = 10\text{V}, I_E = -1\text{mA}, f = 30\text{MHz}$	—	—	25	ps
Transition Frequency	f_T	$V_{CE} = 12.5\text{V}, I_C = 12.5\text{mA}$	300	—	—	MHz
Power Gain (Fig.)	2SC2216	G_{pe} $V_{CC} = 12.5\text{V}, I_E = -12.5\text{mA}, f = 45\text{MHz}$	29	—	36	dB
	2SC2717		28	—	36	

961001EAA2

● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

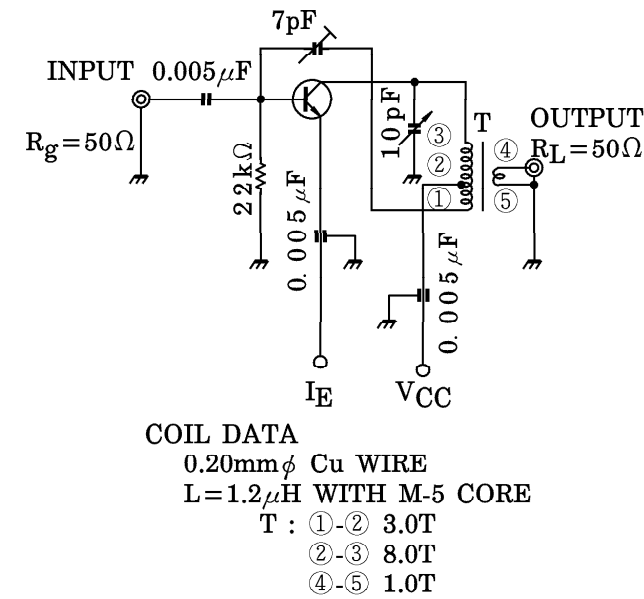
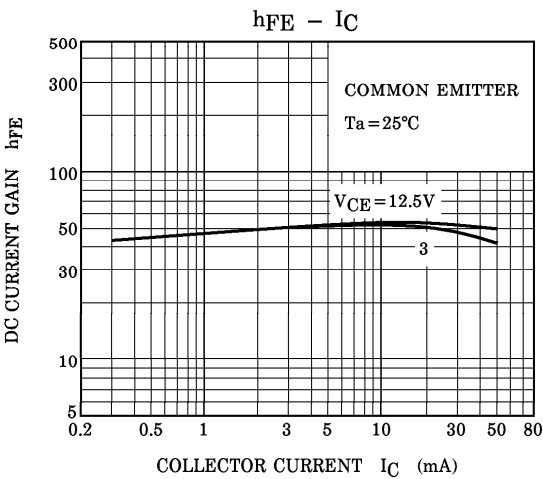
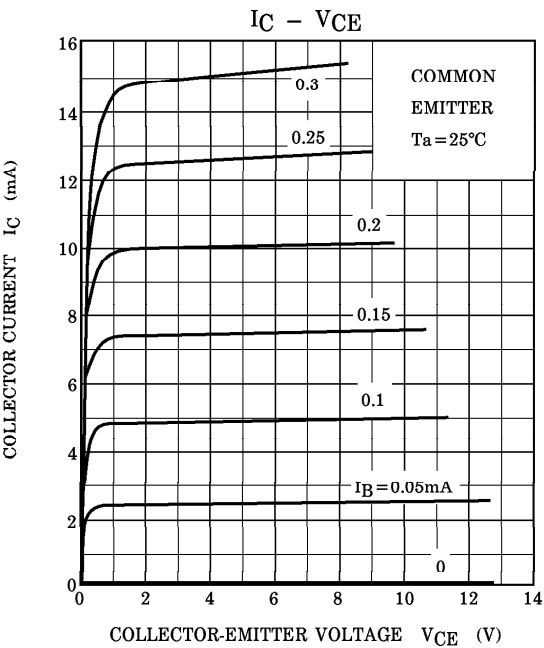
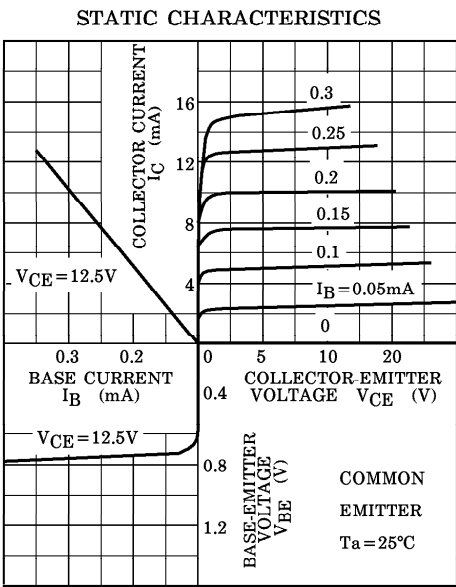


Fig. 45MHz G_{pe} TEST CIRCUIT



961001EAA2'

● The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

● The information contained herein is subject to change without notice.

